



STD123ASF

NPN Silicon Transistor

Features

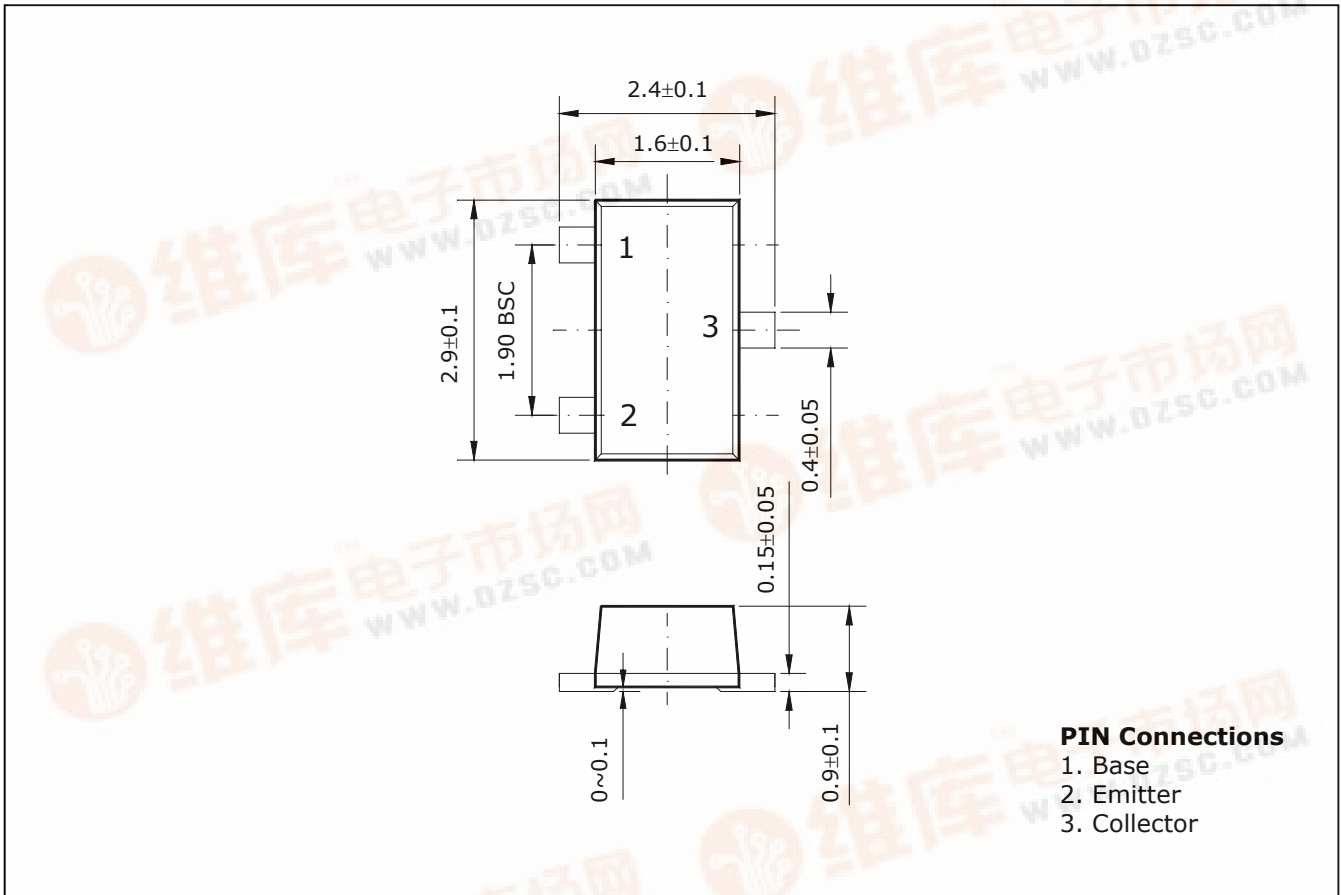
- High β & low saturation transistor.
 $h_{FE}=400$ Min. @ $V_{CE}=1V, I_c=100mA$
- Suitable for large current drive directly.
- Application for IRED Drive transistor in remote transmitter.

Ordering Information

Type NO.	Marking	Package Code
STD123ASF	12A	SOT-23F

Outline Dimensions

unit : mm



Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	10	V
Collector-Emitter voltage	V_{CEO}	6	V
Emitter-Base voltage	V_{EBO}	3	V
Collector current	I_C	1	A
Collector dissipation	P_C^*	350	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

* : Package mounted on 99.5% alumina 10×8×0.1mm

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV_{CBO}	$I_C=50\mu A, I_E=0$	10	-	-	V
Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=1mA, I_B=0$	6	-	-	V
Emitter-Base breakdown voltage	BV_{EBO}	$I_E=50\mu A, I_C=0$	3	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=10V, I_E=0$	-	-	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$	-	-	0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	400	-	-	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	0.1	0.3	V
Transistor frequency	f_T	$V_{CE}=5V, I_C=50mA$	-	260	-	MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	5	-	pF
On resistance	R_{ON}	$f=1KHz, I_B=1mA, V_{IN}=0.3V$	-	0.6	-	Ω

Electrical Characteristic Curves

Fig. 1 $P_C - T_a$

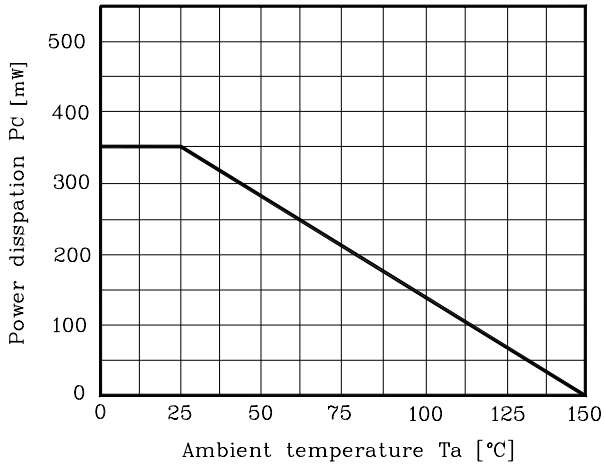


Fig. 2 $V_{CE(sat)} - I_C$

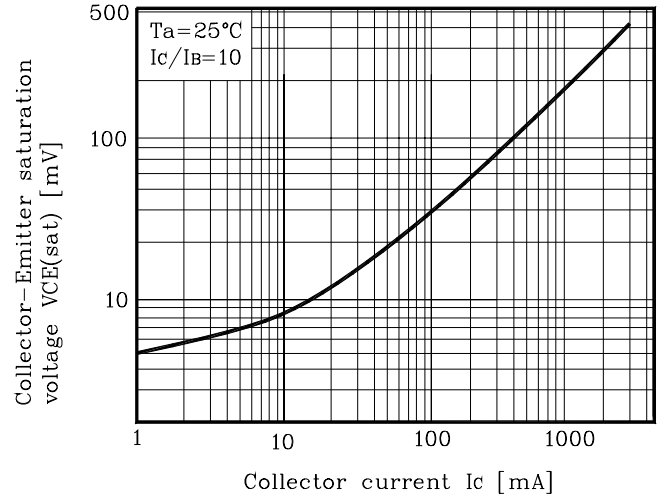


Fig. 3 $C_{ob} - V_{CB}$

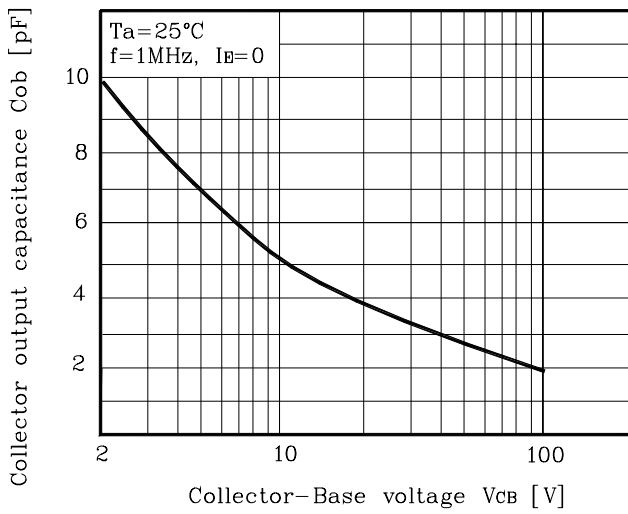


Fig. 4 $h_{FE} - I_C$

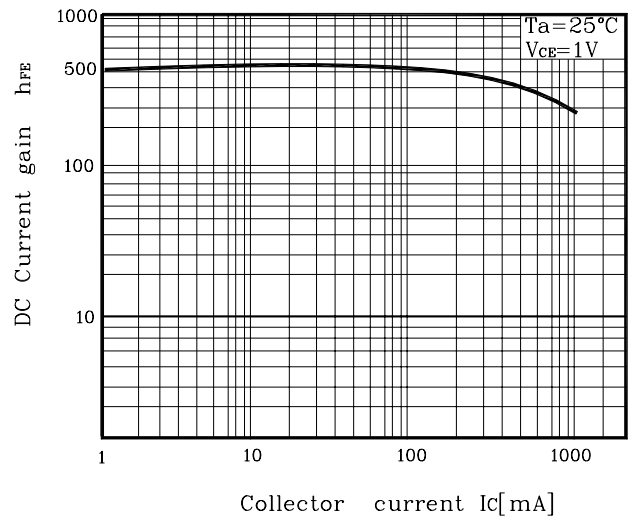


Fig. 5 $R_{ON} - I_B$

